2 1534 (flash adj memory) and (ion adj implant\$4) US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	04/07/16 14:07 04/07/16 15:00 04/07/16 13:17 04/07/16 13:40
2 1534 (flash adj memory) and (ion adj implant\$4) USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB 3 541 ((flash adj memory) and (ion adj implant\$4)) and anneal\$4 USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB 4 430 (((flash adj memory) and (ion adj implant\$4)) and anneal\$4) uSPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB 4 430 ((((flash adj memory) and (ion adj implant\$4)) and anneal\$4) uSPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB 5 277 (((((flash adj memory) and (ion adj implant\$4)) and anneal\$4) and (isollat\$4 or insulat\$4)) and (gate adj electrode) USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB 6 0 ((((flash adj memory) and (ion adj implant\$4)) and anneal\$4) and (isollat\$4 or insulat\$4)) and ((gate adj electrode) same (tunnel adj oxide) same (floating adj gate) same (control adj EPO; JPO;	04/07/16 13:17 04/07/16 13:40
2 1534 (flash adj memory) and (ion adj implant\$4) 3 541 ((flash adj memory) and (ion adj implant\$4)) and anneal\$4 USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; IMDED USPAT; US-PGPUB; IMDED USPAT; US-	04/07/16 13:17 04/07/16 13:40
2 1534 (flash adj memory) and (ion adj implant\$4) 3 541 ((flash adj memory) and (ion adj implant\$4)) and anneal\$4 USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM	04/07/16 13:17 04/07/16 13:40
2	04/07/16 13:17 04/07/16 13:40
US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; ISM_TDB USPAT; US-PGPUB; EPO; JPO; JPO; JPO; JPO; JPO; JPO; JPO; J	04/07/16 13:17 04/07/16 13:40
541 ((flash adj memory) and (ion adj implant\$4)) and anneal\$4 USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; US-PGPUB; EPO; US-PGPUB; EPO; US-PGPUB; EPO; US-PGPUB; EPO; US-PG	04/07/16 13:40
3 541 ((flash adj memory) and (ion adj implant\$4)) and anneal\$4 USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB US	04/07/16 13:40
3 541 ((flash adj memory) and (ion adj implant\$4)) and anneal\$4 USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB 4 430 (((flash adj memory) and (ion adj implant\$4)) and anneal\$4) USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB 5 277 ((((flash adj memory) and (ion adj implant\$4)) and anneal\$4) uSPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB 1 USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB 2 USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB 3 ((((flash adj memory) and (ion adj implant\$4)) and anneal\$4) and (isollat\$4 or insulat\$4)) and ((gate adj electrode) same (tunnel adj oxide) same (floating adj gate) same (control adj EPO; JPO;	04/07/16 13:40
(((flash adj memory) and (ion adj implant\$4)) and anneal\$4 ((((flash adj memory) and (ion adj implant\$4)) and anneal\$4) ((((flash adj memory) and (ion adj implant\$4)) and anneal\$4) and (isollat\$4 or insulat\$4) (((((flash adj memory) and (ion adj implant\$4)) and anneal\$4) and (isollat\$4 or insulat\$4)) and (gate adj electrode) (((((flash adj memory) and (ion adj implant\$4)) and anneal\$4) and (isollat\$4 or insulat\$4)) and ((gate adj electrode) same (tunnel adj oxide) same (floating adj gate) same (control adj (() JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	04/07/16 13:40
4 430 (((flash adj memory) and (ion adj implant\$4)) and anneal\$4) and (isollat\$4 or insulat\$4) 5 277 ((((flash adj memory) and (ion adj implant\$4)) and anneal\$4) and (isollat\$4 or insulat\$4)) and (gate adj electrode) 6 0 ((((flash adj memory) and (ion adj implant\$4)) and anneal\$4) and (isollat\$4 or insulat\$4)) and (gate adj electrode) 6 0 ((((flash adj memory) and (ion adj implant\$4)) and anneal\$4) and (isollat\$4 or insulat\$4)) and ((gate adj electrode) same (tunnel adj oxide) same (floating adj gate) same (control adj EPO; JPO;	04/07/16 13:40
4 430 ((((flash adj memory) and (ion adj implant\$4)) and anneal\$4) uspat; lbM_TDB	
4 430 (((flash adj memory) and (ion adj implant\$4)) and anneal\$4) uSPAT; uS-PGPUB; EPO; JPO; DERWENT; IBM_TDB 5 277 ((((flash adj memory) and (ion adj implant\$4)) and anneal\$4) and (isollat\$4 or insulat\$4)) and (gate adj electrode) 6 0 ((((flash adj memory) and (ion adj implant\$4)) and anneal\$4) and (isollat\$4 or insulat\$4)) and (ion adj implant\$4)) and anneal\$4) and (isollat\$4 or insulat\$4)) and ((gate adj electrode) same (tunnel adj oxide) same (floating adj gate) same (control adj DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
4 430 ((((flash adj memory) and (ion adj implant\$4)) and anneal\$4) and (isollat\$4 or insulat\$4) 5 277 (((((flash adj memory) and (ion adj implant\$4)) and anneal\$4) and (isollat\$4 or insulat\$4)) and (gate adj electrode) 6 0 (((((flash adj memory) and (ion adj implant\$4)) and anneal\$4) and (isollat\$4 or insulat\$4)) and ((gate adj electrode) and (isollat\$4 or insulat\$4)) and ((gate adj electrode) same (tunnel adj oxide) same (floating adj gate) same (control adj EPO; JPO;	
430 ((((flash adj memory) and (ion adj implant\$4)) and anneal\$4) and (isollat\$4 or insulat\$4) 5 277 ((((flash adj memory) and (ion adj implant\$4)) and anneal\$4) and (isollat\$4 or insulat\$4)) and (gate adj electrode) 6 0 ((((flash adj memory) and (ion adj implant\$4)) and anneal\$4) and (isollat\$4 or insulat\$4)) and ((gate adj electrode) uspart; lbm_TDB uspart; lbm	
and (isollat\$4 or insulat\$4) US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; ISPO; IS	
5 277 ((((flash adj memory) and (ion adj implant\$4)) and anneal\$4) and (isollat\$4 or insulat\$4)) and (gate adj electrode) 0 ((((flash adj memory) and (ion adj implant\$4)) and anneal\$4) and (isollat\$4 or insulat\$4)) and ((gate adj electrode) and (isollat\$4 or insulat\$4)) and ((gate adj electrode) same (tunnel adj oxide) same (floating adj gate) same (control adj EPO; JPO;	04/07/16 13:40
5 277 (((((flash adj memory) and (ion adj implant\$4)) and anneal\$4) and (isollat\$4 or insulat\$4)) and (gate adj electrode) 0 (((((flash adj memory) and (ion adj implant\$4)) and anneal\$4) and (isollat\$4 or insulat\$4)) and ((gate adj electrode) same (tunnel adj oxide) same (floating adj gate) same (control adj EPO; JPO;	04/07/16 13:40
6 0 (((((flash adj memory) and (ion adj implant\$4)) and anneal\$4) and (isollat\$4 or insulat\$4)) and (gate adj electrode) 0 (((((flash adj memory) and (ion adj implant\$4)) and anneal\$4) and (isollat\$4 or insulat\$4)) and ((gate adj electrode) same (tunnel adj oxide) same (floating adj gate) same (control adj EPO; JPO;	04/07/16 13:40
((((flash adj memory) and (ion adj implant\$4)) and anneal\$4) USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; and (isollat\$4 or insulat\$4)) and (ion adj implant\$4)) and anneal\$4) and (isollat\$4 or insulat\$4)) and ((gate adj electrode) same (tunnel adj oxide) same (floating adj gate) same (control adj EPO; JPO;	04/07/16 13:40
and (isollat\$4 or insulat\$4)) and (gate adj electrode) US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; and (isollat\$4 or insulat\$4)) and ((gate adj electrode) same (tunnel adj oxide) same (floating adj gate) same (control adj EPO; JPO;	
6 0 ((((flash adj memory) and (ion adj implant\$4)) and anneal\$4) and (isollat\$4 or insulat\$4)) and ((gate adj electrode) same (tunnel adj oxide) same (floating adj gate) same (control adj	
6 0 ((((flash adj memory) and (ion adj implant\$4)) and anneal\$4) uSPAT; and (isollat\$4 or insulat\$4)) and ((gate adj electrode) same (tunnel adj oxide) same (floating adj gate) same (control adj EPO; JPO;	•
6 0 ((((flash adj memory) and (ion adj implant\$4)) and anneal\$4) USPAT; 200 and (isollat\$4 or insulat\$4)) and ((gate adj electrode) same (US-PGPUB; EPO; JPO; US-PGPUB; EPO; JPO;	
and (isollat\$4 or insulat\$4)) and ((gate adj electrode) same US-PGPUB; (tunnel adj oxide) same (floating adj gate) same (control adj EPO; JPO;	
(tunnel adj oxide) same (floating adj gate) same (control adj EPO; JPO;	04/07/16 12:05
gate) same (active adj area))	
IBM_TDB	
	04/07/16 12:06
anneal\$4) and (isollat\$4 or insulat\$4)) and (gate adj US-PGPUB;	
electrode)) and (tunnel adj oxide) and (floating adj gate) and EPO; JPO;	
(control adj gate) and (active adj area) DERWENT;	
9 11 (((((((flash adj memory) and (ion adj implant\$4)) and USPAT; 200	04/07/16 12:07
9 11 ((((((flash adj memory) and (ion adj implant\$4)) and USPAT; 200 anneal\$4) and (isollat\$4 or insulat\$4)) and (gate adj US-PGPUB;	04/07/10 12.07
electrode)) and (tunnel adj oxide) and (floating adj gate) and EPO; JPO;	
(control adj gate) and (active adj area)) and ((doped adj DERWENT;	
drain) or DDD)	
	04/07/16 13:18
US-PGPUB;	
EPO; JPO;	
DERWENT;	
IBM_TDB	
	04/07/16 13:19
anneal\$4) and (isollat\$4 or insulat\$4)) and (gate adj US-PGPUB;	
electrode)) and (tunnel adj oxide) and (floating adj gate) and EPO; JPO;	
(control adj gate) and (active adj area)) and ((ion adj DERWENT;	
implant\$4) with anneal\$4) IBM_TDB	24/07/10 15 11
	04/07/16 13:41
anneal\$4) and (isollat\$4 or insulat\$4)) and (gate adj US-PGPUB;	
electrode)) and ((ion adj implant\$4) with anneal\$4) EPO; JPO;	
DERWENT; IBM TDB	
	04/07/16 13:30
anneal\$4) and (isollat\$4 or insulat\$4)) and (gate adj US-PGPUB;	UC.SI ULIUI F
electrode)) and (((ion adj implant\$4)) with anneal\$4) same	
(ammonia or hydrogen or nitrogen))	
IBM_TDB	

15	0	(((((flash adj memory) and (ion adj implant\$4)) and	USPAT;	2004/07/16 13:30
		anneal\$4) and (isollat\$4 or insulat\$4)) and (gate adj	US-PGPUB;	
1		electrode)) and (((ion adj implant\$4) with anneal\$4) same	EPO; JPO;	
İ		(ammonia or hydrogen or nitrogen))	DERWENT;	
	45	////61 als add as a second of the add the add 400 and	IBM_TDB	0004/07/40 44-50
14	15	((((((flash adj memory) and (ion adj implant\$4))) and	USPAT;	2004/07/16 14:59
		anneal\$4) and (isollat\$4 or insulat\$4)) and (gate adj	US-PGPUB;	,
		electrode)) and ((ion adj implant\$4) with anneal\$4) and	EPO; JPO;	
		(ammonia or hydrogen or nitrogen)	DERWENT; IBM_TDB	
16	430	(((flash adj memory) and (ion adj implant\$4)) and anneal\$4)	USPAT;	2004/07/16 13:40
10	430	and (isollat\$4 or insulat\$4)	US-PGPUB;	2004/07/10 15.40
		and (isoliator of insulator)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
17	277	(((((flash adj memory) and (ion adj implant\$4)) and anneal\$4)	USPAT;	2004/07/16 13:41
''		and (isollat\$4 or insulat\$4)) and (gate adj electrode)	US-PGPUB;	200 1/0//10 10:11
		(somety to modulate ty) and (gate any stocked)	EPO; JPO;	
			DERWENT:	
			IBM_TDB	
18	15	(((((flash adj memory) and (ion adj implant\$4)) and	USPAT;	2004/07/16 13:42
		anneal\$4) and (isollat\$4 or insulat\$4)) and (gate adj	US-PGPUB;	
		electrode)) and ((ion adj implant\$4) with anneal\$4) and	EPO; JPO;	
		(ammonia or hydrogen or nitrogen)	DERWENT;	
			IBM_TDB	
19	15	(((((flash adj memory) and (ion adj implant\$4)) and	USPAT;	2004/07/16 13:42
		anneal\$4) and (isollat\$4 or insulat\$4)) and (gate adj	US-PGPUB;	
		electrode)) and ((ion adj implant\$4) with anneal\$4) and	EPO; JPO;	
		(ammonia or hydrogen or nitrogen)	DERWENT;	
	50705		IBM_TDB	
20	56795	flash adj memory	USPAT;	2004/07/16 14:07
			US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM_TDB	
21	0	 (flash adj memory) and ((ion adj implant\$4) same ((spike or	USPAT;	2004/07/16 14:12
-	J	repid) adj2 anneal\$4) same (ammonium or hydrogen or	US-PGPUB;	2004/07/10 14.12
		nitrogen))	EPO; JPO;	
		······•ge///	DERWENT:	
İ			IBM TDB	
23	34	(flash adj memory) and (ion adj implant\$4) and (((spike or	USPAT;	2004/07/16 14:19
		rapid) adj2 anneal\$4) same (ammonium or hydrogen or	US-PGPUB;	
		nitrogen))	EPO; JPO;	
i			DERWENT;	
			IBM_TDB	
25	34	(flash adj memory) and (ion adj implant\$4) and (((spike or	USPAT;	2004/07/16 14:19
		rapid) adj2 anneal\$4) same (ammonium or hydrogen or	US-PGPUB;	
		nitrogen)) and implant\$4	EPO; JPO;	
			DERWENT;	
26	0	((flash adj memory) and (ion adj implant\$4) and (((spike or	IBM_TDB USPAT;	2004/07/16 14:59
~~	١	rapid) adj2 anneal\$4) same (ammonium or hydrogen or	US-PGPUB;	2004/07/10 14:59
		nitrogen)) and implant\$4) and (heat\$4 adj rate)	EPO; JPO;	
		Third ogerij) and implantory and (heator adjuate)	DERWENT;	
			IBM_TDB	
27	0	(flash adj memory) and (ion adj implant\$4) and (((rapid or	USPAT;	2004/07/16 15:04
	_	spike) adj3 anneal\$4) with (heat\$4 adj rate))	US-PGPUB;	
			EPO; JPO;	
		•	DERWENT;	
			IBM_TDB	
28	0	(flash adj memory) and (ion adj implant\$4) and (((rapid or	USPAT;	2004/07/16 15:04
	ļ	spike) adj3 anneal\$4) same (heat\$4 adj rate))	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	<u>_</u> l		IBM_TDB	

29	1	(flash adj memory) and (ion adj implant\$4) and (anneal\$4	USPAT;	2004/07/16 15:04
		same (heat\$4 adj rate))	US-PGPUB;	
			EPO; JPO;	
		·	DERWENT;	
			IBM TDB	